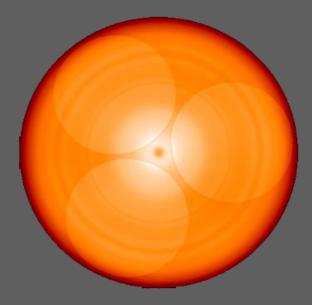


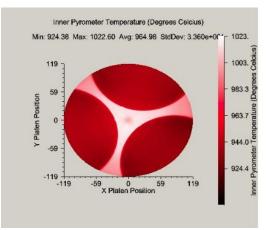
Full Carrier Temperature Maps at the Click of a Button!

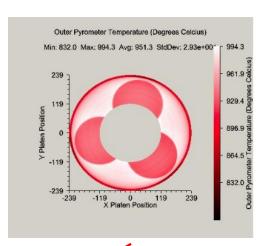


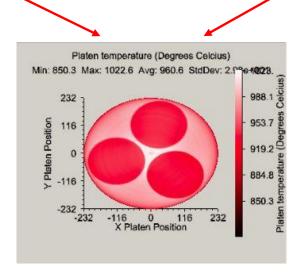


- Quickly, easily, and accurately generate full carrier temperature maps
- Determine temperature uniformity, adjust heater zones, easily see hot and cold areas
- Two calibrated sensor heads enable full center to edge scans in under two minutes on Veeco 465i reactor



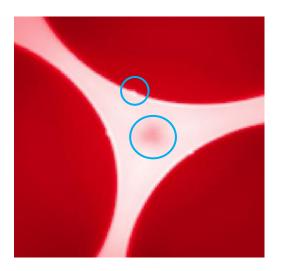






Carrier map with 200mm silicon wafers

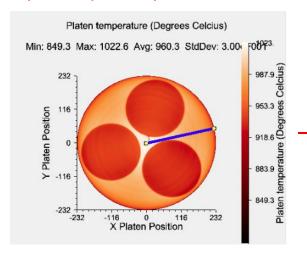
Two pyrometer heads combine to provide a *FULL* center-to-edge temperature map from a single scan

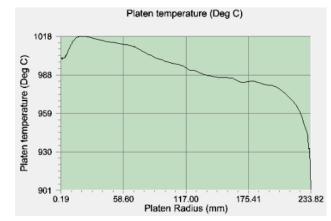


Angular resolution of 0.3 or better resolves even the finest details such as wafer notches and cold spot due to spindle as shown above

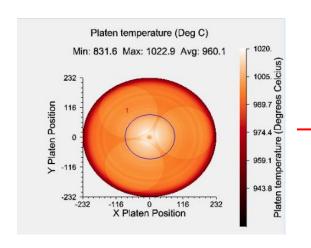


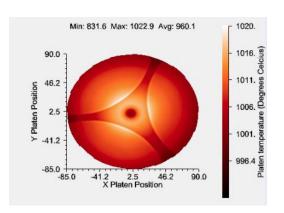
Analysis Capability





User selectable line profile - any position, length and line width

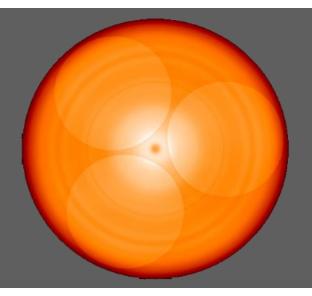




User selectable area maps for zoom-in analysis capability



Complete Carrier Temperature Characterization



Functional Specifications

Applicable MOCVD reactors	k465i, Epik 700
Scan range	Full carrier, or any subset specified by the user
Temperature range	530 – 1250°C (higher temperature range units available upon request, e.g. for AIN applications)
Temperature resolution	0.5°C or better at growth temperature
Scan resolution	User selectable. Typical radial scan step size: 1mm. Angular resolution: 0.3° or better.
Scan time	100 seconds for full carrier scan on k465i with 1mm radial step resolution.